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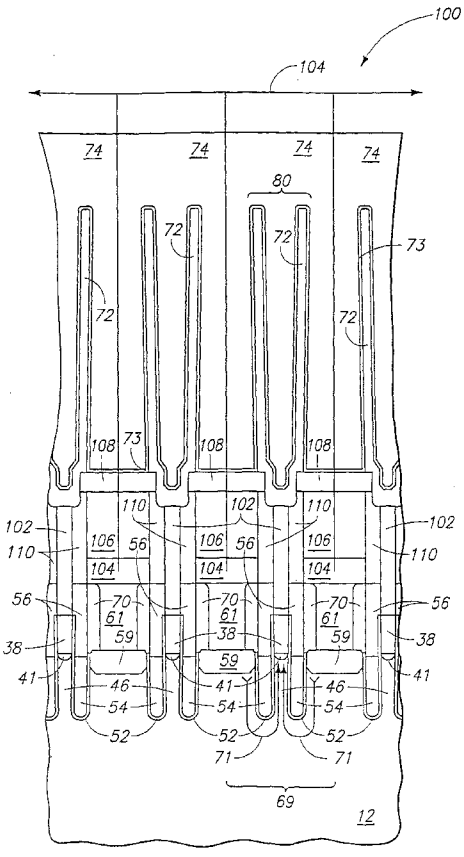
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*[Continued on next page]*

(54) Title: DRAM TRANSISTOR WITH A GATE BURIED IN THE SUBSTRATE AND METHOD OF FORMING THEREOF




(57) Abstract: The invention includes a transistor device (69) having a semiconductor substrate (12) with an upper surface. A pair of source/drain regions (41,59) are formed within the semiconductor substrate and a channel region (46) is formed within the semiconductor substrate and extends generally perpendicularly relative to the upper surface of the semiconductor substrate. A gate (54) is formed within the semiconductor substrate between the pair of the source/drain regions (41,59), and can surround the channel region (46) and /or one of the source/drain regions.

WO 2006/028775 A3

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